T	77. L.	Coangh Tout	T DB	Time etamn
L Number	Hits	Search Text 	DB	Time stamp
1	139336	second near3 (electrode or anode or cathode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/29 14:04
2	30857	(second near3 (electrode or anode or cathode)) and (second near3 (bias or voltage or potential))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/29 14:09
3	5419	((second near3 (electrode or anode or cathode)) and (second near3 (bias or voltage or potential))) and (alternat\$5 near5 (bias or voltage or potential))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/29 14:05
4	530	<pre>(((second near3 (electrode or anode or cathode)) and (second near3 (bias or voltage or potential))) and (alternat\$5 near5 (bias or voltage or potential)))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/29 14:06
5	186	and pad ((((second near3 (electrode or anode or cathode)) and (second near3 (bias or voltage or potential))) and (alternat\$5 near5 (bias or voltage or potential)))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/29 14:08
6	. 17900	and pad) and (copper or cu) (second near3 (bias or voltage or potential)) same (second near3 (electrode or anode or cathode))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/29 14:10
7	97	<pre>(((((second near3 (electrode or anode or cathode)) and (second near3 (bias or voltage or potential))) and (alternat\$5 near5 (bias or voltage or potential))) and pad) and (copper or cu)) and ((second near3 (bias or voltage or potential)) same (second near3 (electrode or anode or cathode)))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 14:31
8	23152	(electrode or anode or cathode) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8 or electroly\$8 or electrochem\$8) near5 (voltage or bias or potential)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/29 14:38
9	1283	(electrode or anode or cathode) near5 (etch\$8 or electroetch\$8 or polish\$8 or electropolish\$8) near5 (voltage or bias or potential)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/29 14:35
10	315	((electrode or anode or cathode) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8 or electroly\$8 or electrochem\$8) near5 (voltage or bias or potential)) and ((electrode or anode or cathode) near5 (etch\$8 or electroetch\$8 or polish\$8 or electropolish\$8) near5 (voltage or bias or potential))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 14:35
11	52	(((electrode or anode or cathode) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8 or electroly\$8 or electrochem\$8) near5 (voltage or bias or potential)) and ((electrode or anode or cathode) near5 (etch\$8 or electroetch\$8 or polish\$8 or electropolish\$8) near5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 14:35
12 .	25501	<pre>(voltage or bias or potential))) and pad (second\$5 near5 (electrode or anode or cathode)) near35 (second\$5 near5 (voltage or bias or potential))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/29 14:39

13	8	<pre>((((electrode or anode or cathode) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8 or electroly\$8 or electrochem\$8) near5 (voltage or bias or potential)) and ((electrode or anode or</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/29 14:43
		cathode) near5 (etch\$8 or electroetch\$8 or polish\$8 or electropolish\$8) near5 (voltage or bias or potential))) and pad) and ((second\$5 near5 (electrode or anode		
14	28257	or cathode)) near35 (second\$5 near5 (voltage or bias or potential))) (substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO;	2004/01/29 14:46
15	28257	(substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/29 14:47
16	2835	((substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))) and pad	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/29 14:47
17	564	(((substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))) and pad) and (electroplat\$8 or electroly\$8 or electrochem\$8 or	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 14:47
18	397	electrodeposit\$8) ((((substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))) and pad) and (electroplat\$8 or electrodeposit\$8) or electrodeposit\$8) and or cathode or anode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 14:48
19	91	electroetch\$8 or polish\$8 or electropolish\$8) (((((substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))) and pad) and (electroplat\$8 or electroly\$8 or electrochem\$8 or electrodeposit\$8)) and (etch\$8 or electroetch\$8 or polish\$8 or electropolish\$8)) and (second\$5 near3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 14:52
20	5235	<pre>(voltage or bias or potential)) (first or primary or initial) near5 (voltage or bias or potential) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/29 14:54
21	438	(second\$5 or final) near5 (voltage or bias or potential) near5 (etch\$5 or electroetch\$5 or polish\$5 or electropolish\$5)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/29 14:55
22	15586	((first or primary or initial) near5 (voltage or bias or potential) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8) ) nad ((second\$5 or final) near5 (voltage or bias or potential) near5 (etch\$5 or electroetch\$5 or polish\$5 or electropolish\$5) )	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 14:56

23	17	<pre>((first or primary or initial) near5 (voltage or bias or potential) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8) ) and ((second\$5 or final) near5 (voltage or bias or</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 14:56
24	5	potential) near5 (etch\$5 or electroetch\$5 or polish\$5 or electropolish\$5) ) (((first or primary or initial) near5 (voltage or bias or potential) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8) ) and ((second\$5 or final) near5 (voltage or bias or potential) near5 (etch\$5 or electroetch\$5 or polish\$5 or electropolish\$5) )) and pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 14:56

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1	545	(anodes or cathodes or electrodes) same (plating or depositing or electorplating or electrodepositing) same (voltages or biases or potentials)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/29 17:32
3	71	((anodes or cathodes or electrodes) same (plating or depositing or electorplating or electrodepositing) same (voltages or biases or potentials)) and pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/29 17:32